General Description

The G1007 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for power switching application and LED backlighting.

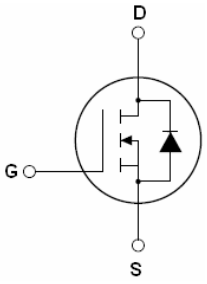
Features

V_{DSS}	$R_{DS(ON)}$ @10V (Typ)	$R_{DS(ON)}$ @4.5V (Typ)	I_D
100V	90 mΩ	95 mΩ	7A

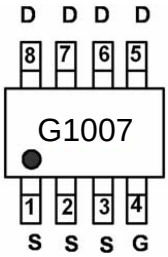
- Ultra Low On-Resistance
- High UIS and UIS 100% Test
- RoHS Compliant

Application

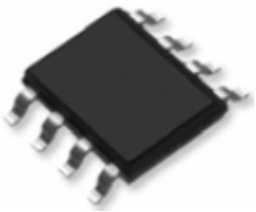
- Power switching application
- LED backlighting



Schematic Diagram



Marking and pin Assignment



SOP-8

Ordering Information

Part Number	Marking	Case	Packaging
G1007	G1007	SOP-8	4000pcs/Reel

Table 1. Absolute Maximum Ratings (TA=25℃)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	100	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±20	V
$I_{D\ (DC)}$	Drain Current (DC) at Tc=25℃	7	A
$I_{D\ (DC)}$	Drain Current (DC) at Tc=100℃	8.5	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed **(Note 1)**	56	A
P_D	Maximum Power Dissipation(Tc=25℃)	28	W
E_{AS}	Single Pulse Avalanche Energy **(Note 2)**	16	mJ
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	℃

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.E_{AS} condition:T_J=25℃,V_{DD}=50V,V_G=10V, R_G=25Ω

Table 2. Thermal Characteristic

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance,Junction-to-Case	3.3	℃/W

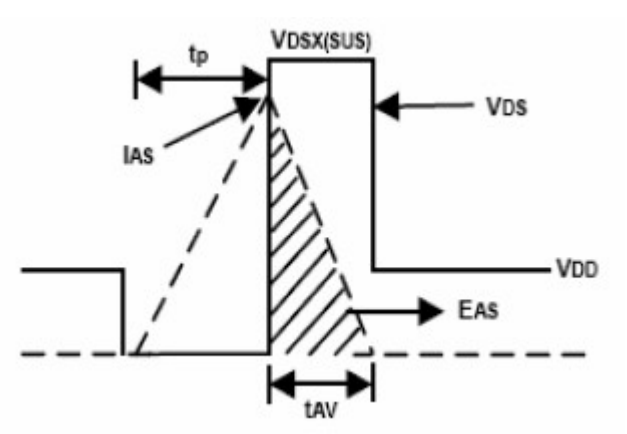
Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

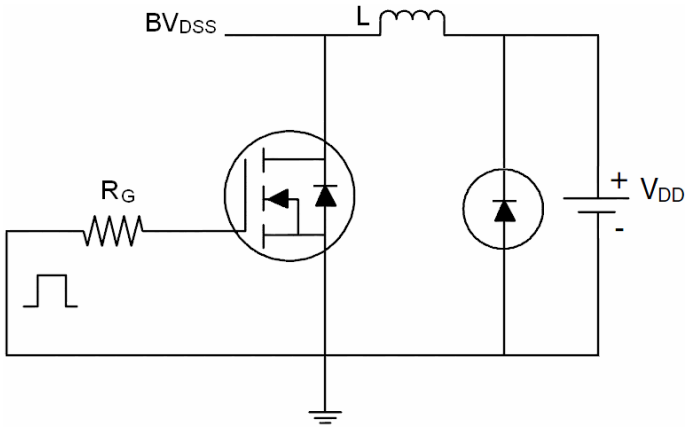
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	100			V
I_{DSS}	Zero Gate Voltage Drain Current(Tc=25℃)	V_{DS}=100V,V_{GS}=0V			1	μA
I_{DSS}	Zero Gate Voltage Drain Current(Tc=100℃)	V_{DS}=100V,V_{GS}=0V			5	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	1	2	3	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=1A		90	110	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=4.5V, I_D=1A		95	120	mΩ
Dynamic Characteristics						
g_{FS}	Forward Transconductance	V_{DS}=5V,I_D=4.5A	5			S
C_{iss}	Input Capacitance	V_{DS}=50V,V_{GS}=0V f=1.0MHz		612		PF
C_{oss}	Output Capacitance			120		PF
C_{rss}	Reverse Transfer Capacitance			91		PF
Q_g	Total Gate Charge	V_{DS}=50V,I_D=4.5A V_{GS}=10V		11		nC
Q_{gs}	Gate-Source Charge			1.9		nC
Q_{gd}	Gate-Drain Charge			2.8		nC
Switching Times						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=50V,R_L=8.6Ω V_{GS}=10V,R_G=3Ω		8		nS
t_r	Turn-on Rise Time			3		nS
$t_{d(off)}$	Turn-Off Delay Time			17		nS
t_f	Turn-Off Fall Time			4.5		nS
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current(Body Diode)			7		A
I_{SDM}	Pulsed Source-Drain Current(Body Diode)			28		A
V_{SD}	Forward On Voltage**(Note 1)**	T_J=25℃,I_{SD}=3A,V_{GS}=0V		0.82	1	V
t_{rr}	Reverse Recovery Time**(Note 1)**	T_J=25℃,I_F=4.5A di/dt=500A/μs		21		nS
Q_{rr}	Reverse Recovery Charge**(Note 1)**			97		nC
t_{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible(turn-on is dominated by L_S+L_D)				

Notes 1.Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 1.5%, Starting T_J=25℃

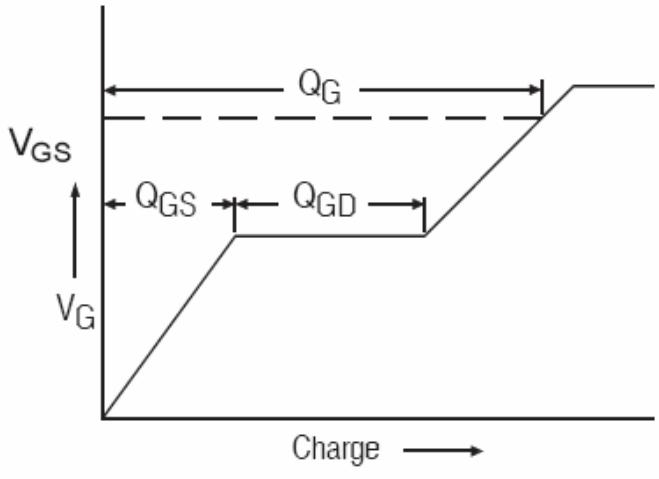
Test Circuit

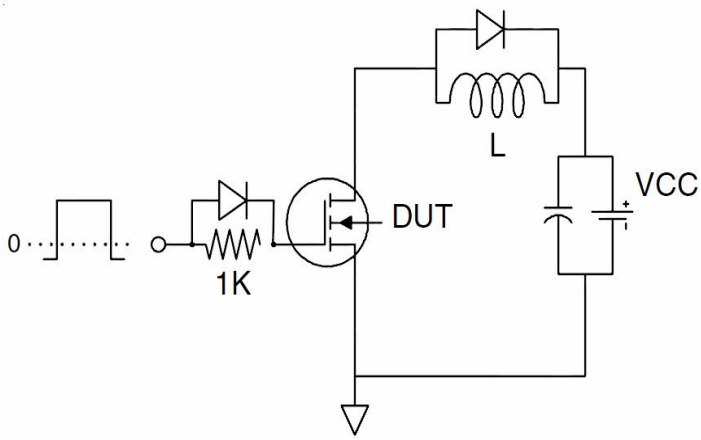
1) E_{AS} Test Circuits



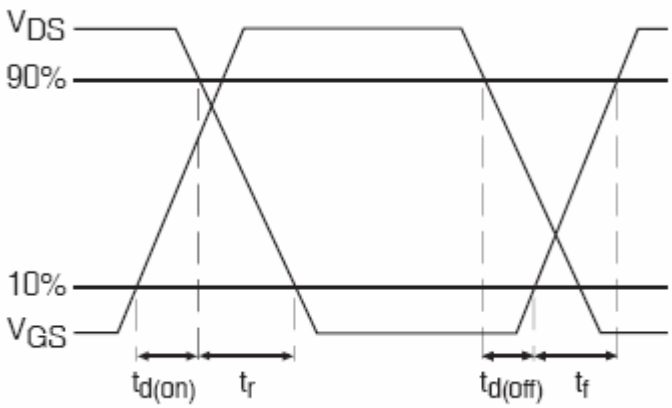


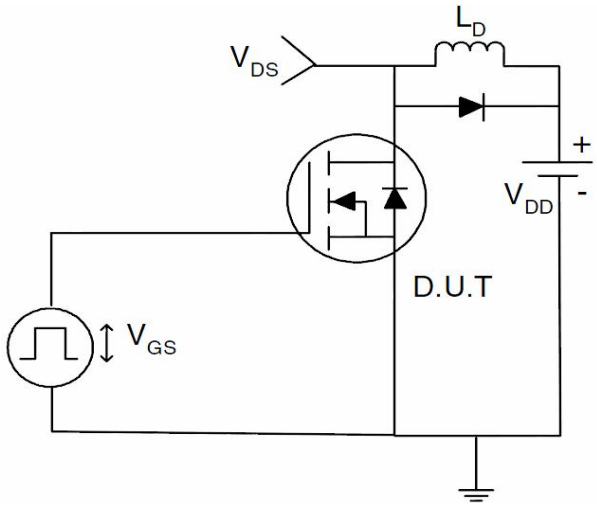
2) Gate Charge Test Circuit:





3) Switch Time Test Circuit:





TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

Figure1. On-Region Characteristics

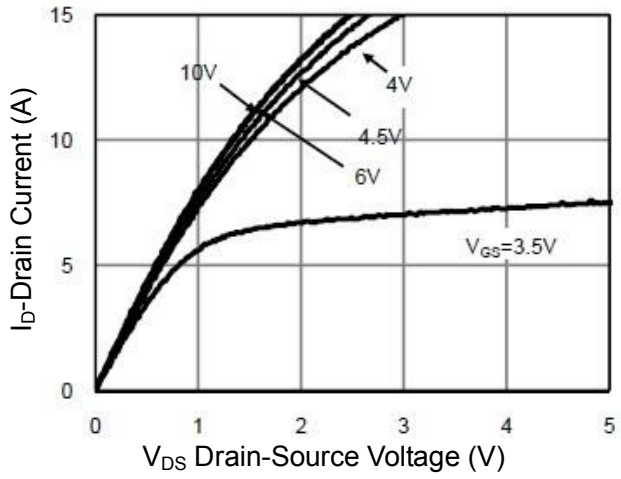


Figure 2: Transfer Characteristics

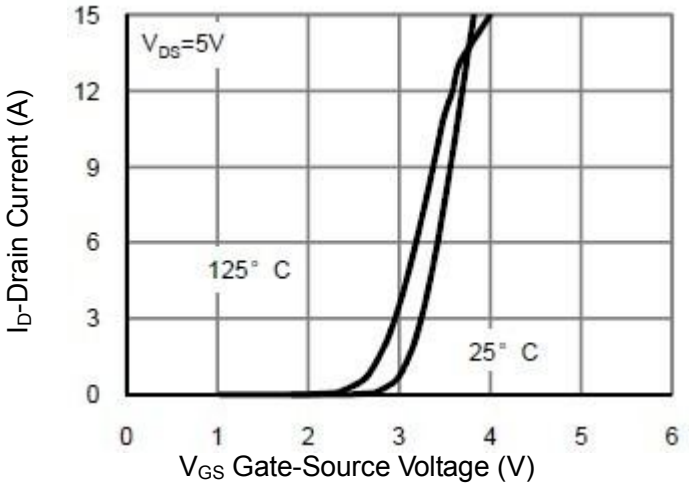


Figure3. On-Resistance vs. Drain Current and Gate Voltage

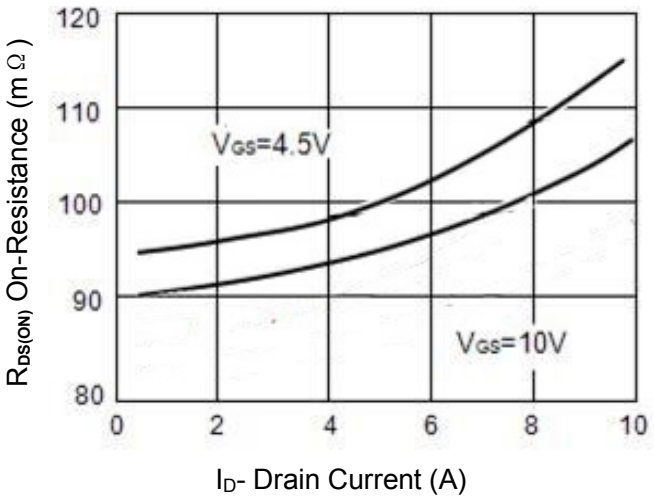


Figure4. On-Resistance vs. Junction Temperature

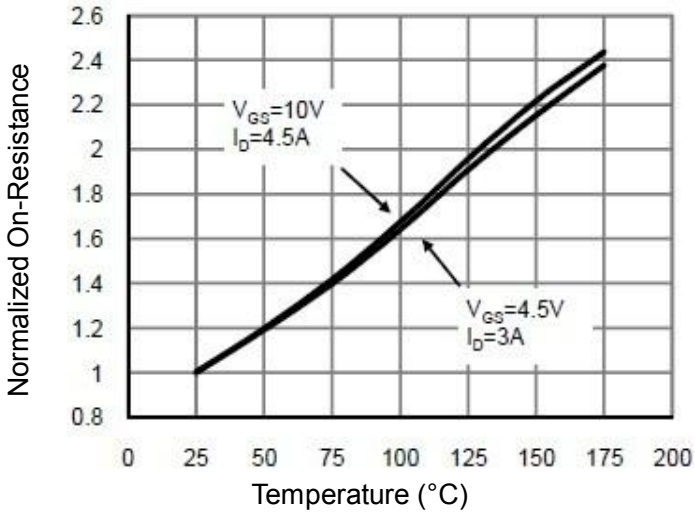


Figure5. On-Resistance vs. Gate-Source Voltage

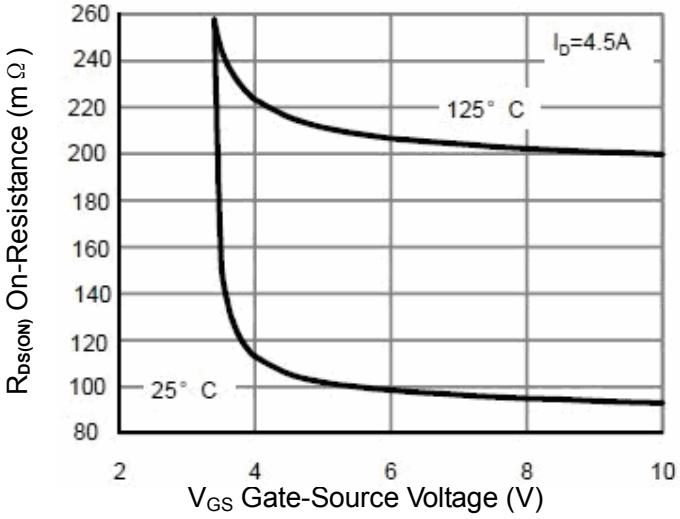


Figure6. Body-Diode Characteristics

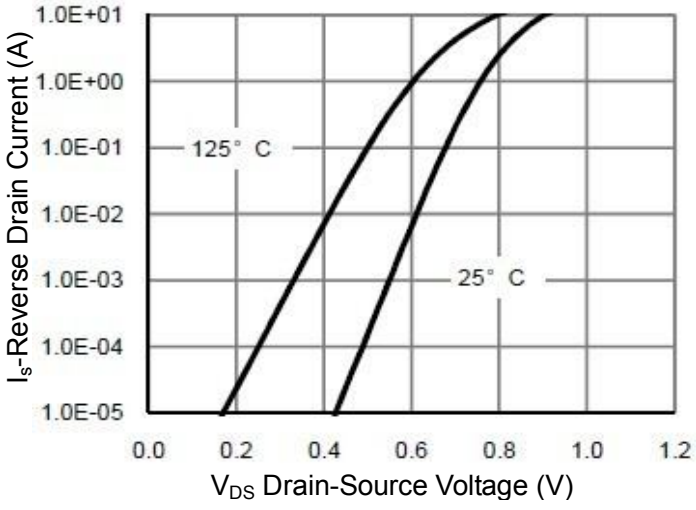


Figure7. Gate-Charge Characteristics

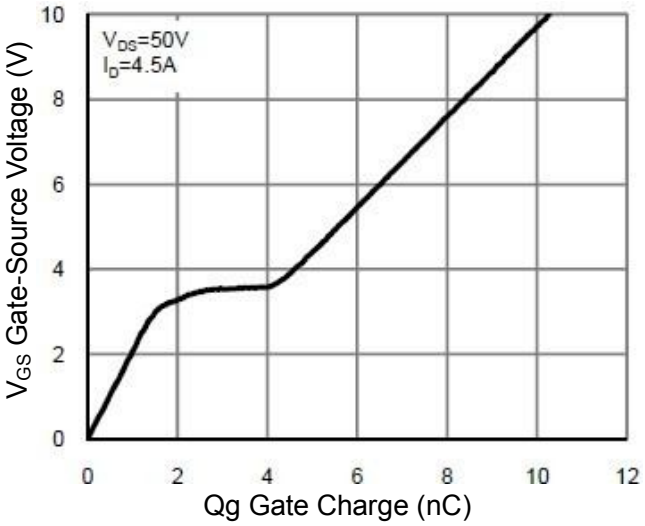


Figure 8. Capacitance Characteristics

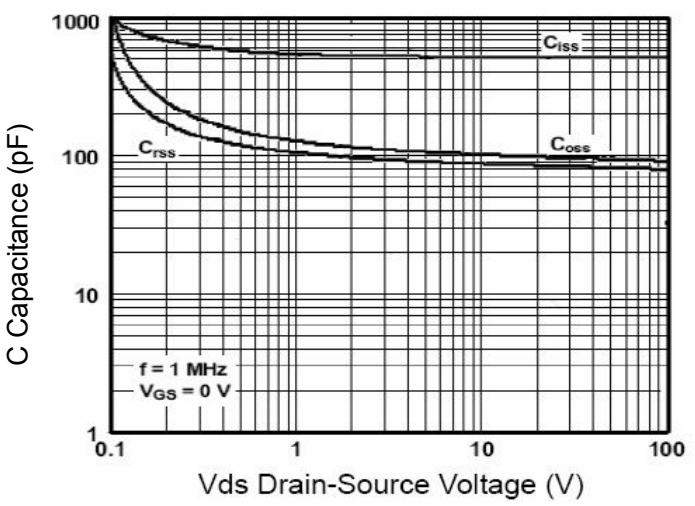


Figure 9. Maximum Forward Biased Safe Operating Area

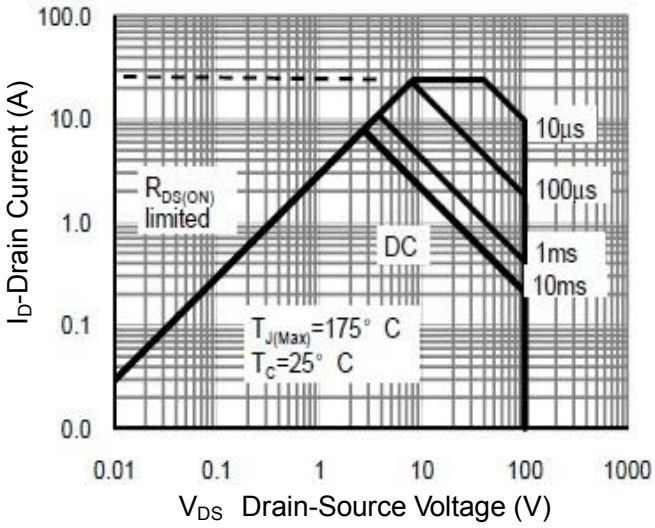


Figure10. Single Pulse Power Rating Junction-to-Case

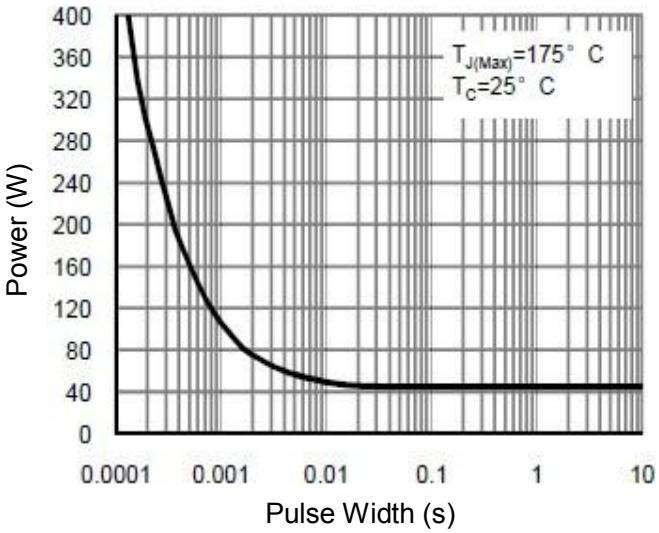
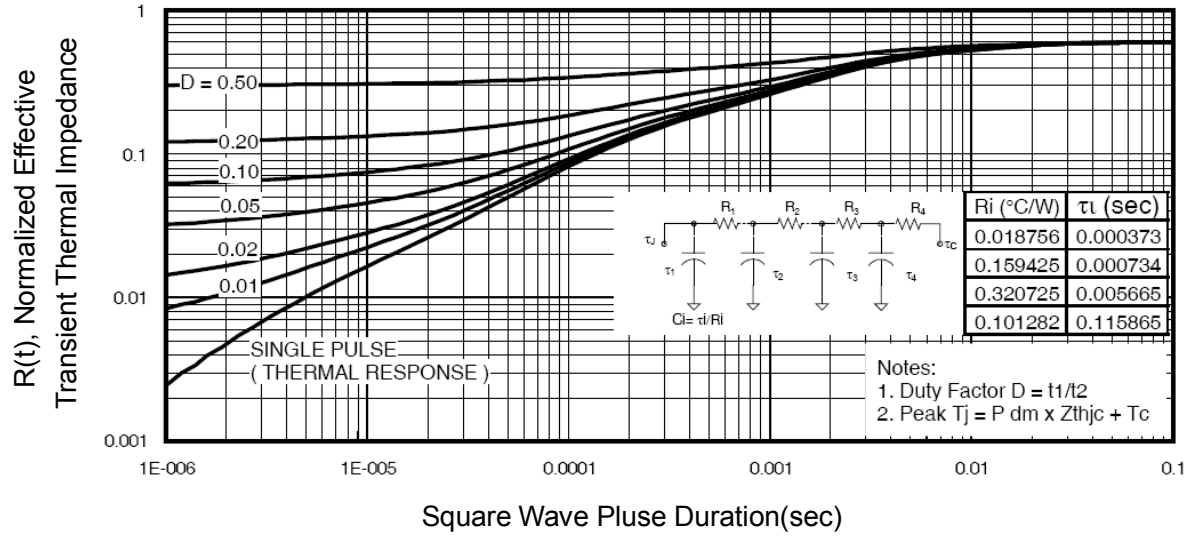
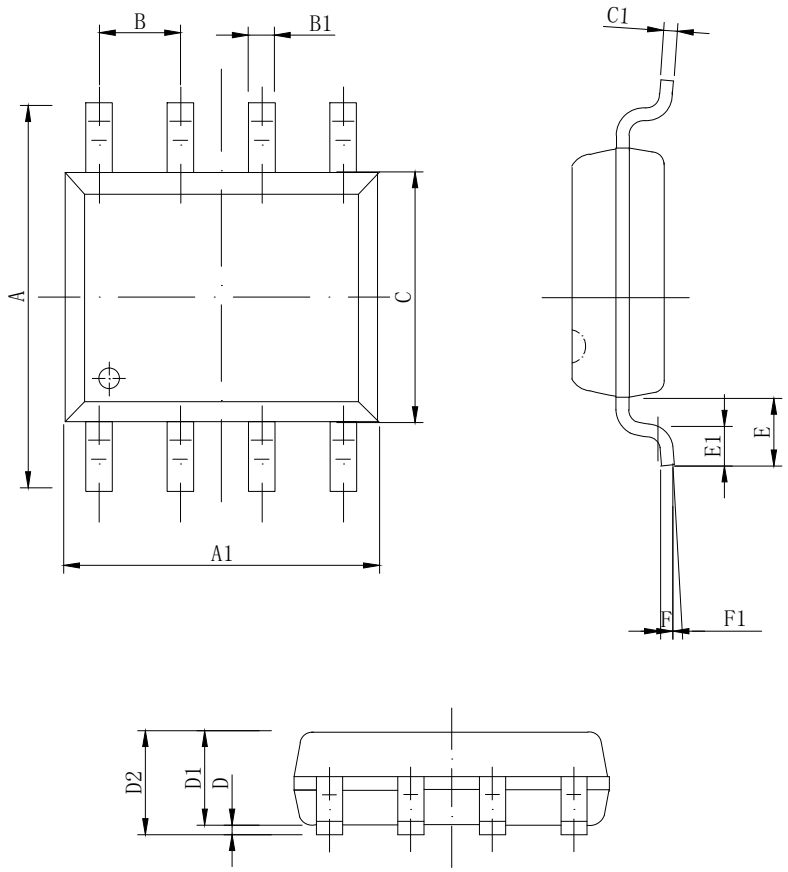


Figure11. Normalized Maximum Transient Thermal Impedance



SOP-8 Package information



DIM	MIN	NOM	MAX
A	5.800	6.000	6.200
A1	4.800	4.900	5.000
B		1.270BSC	
B1	0.35 ^ 8x	0.40 ^ 8x	0.45 ^ 8x
C	3.780	3.880	3.980
C1	-	0.203	0.253
D	0.050	0.150	0.250
D1	1.350	1.450	1.550
D2	1.500	1.600	1.700
E		1.060 REF	
E1	0.400	0.700	0.100
F		0.250BSC	
F1	2°	4°	6°

All Dimensions in mm